## NSN 5962-01-168-5838

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### **Body Length:** 0.960 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 715.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Bipolar and programmable and schottky and monolithic **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 12 input **Case Outline Source And Designator:** D-6 mil-m-38510 **Terminal Surface Treatment:** Solder Voltage Rating And Type Per Characteristic: -0.5 volts power source and 7.0 volts power source **Time Rating Per Chacteristic:** 125.00 nanoseconds propagation delay time, low to high level output and 125.00 nanoseconds propagation delay time, high to low level output Memory Device Type: Rom

#### Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

#### Terminal Type And Quantity:

18 printed circuit

#### Shelf Life:

N/a

#### Unit Of Measure:

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- Demilitarization:

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**Fiig:** A458a0

